

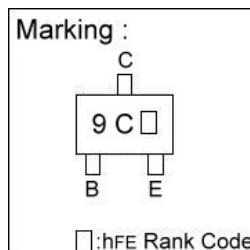
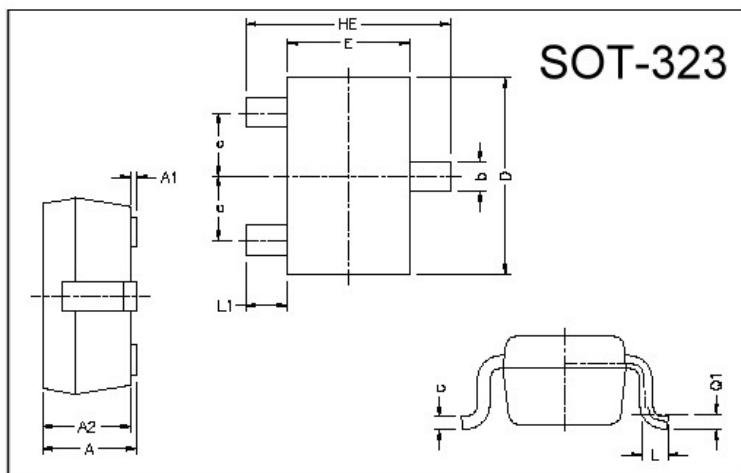
GSBC858

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GSBC858 is designed for switching and AF amplifier application, suitable for automatic insertion in thick and thin-film circuits.

Package Dimensions



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 0.80 | 1.10 | L1 | 0.42 REF. | |
| A1 | 0 | 0.10 | L | 0.15 | 0.35 |
| A2 | 0.80 | 1.00 | b | 0.25 | 0.40 |
| D | 1.80 | 2.20 | c | 0.10 | 0.25 |
| E | 1.15 | 1.35 | e | 0.65 REF. | |
| HE | 1.80 | 2.40 | Q1 | 0.15 BSC. | |

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|------------|------|
| Junction Temperature | T _j | +150 | °C |
| Storage Temperature | T _{stg} | -55 ~ +150 | °C |
| Collector to Base Voltage | VCBO | -30 | V |
| Collector to Emitter Voltage | VCEO | -30 | V |
| Emitter to Base Voltage | VEBO | -5 | V |
| Collector Current | I _C | 100 | mA |
| Total Power Dissipation | PD | 225 | mW |

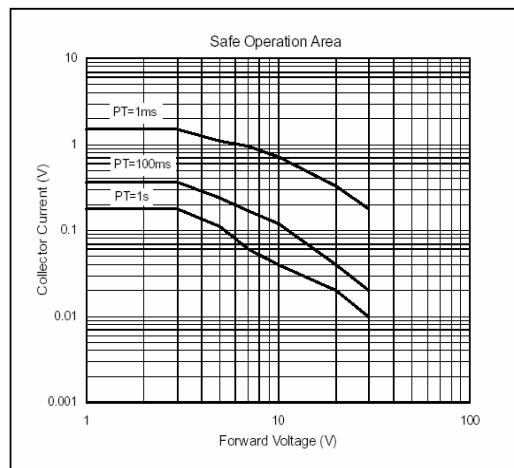
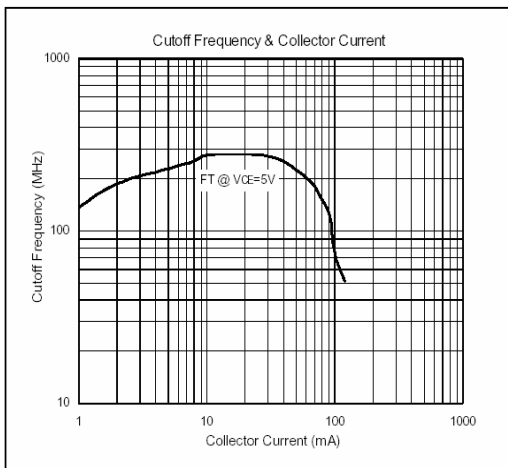
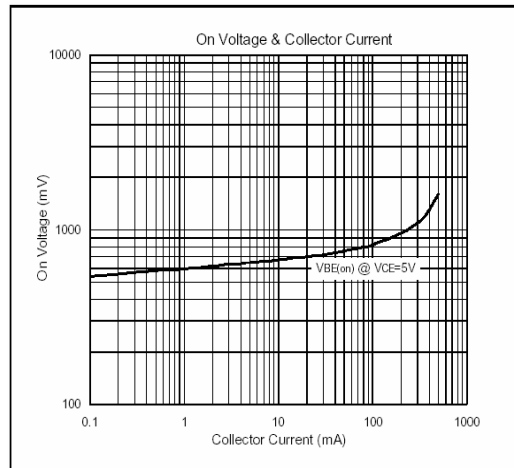
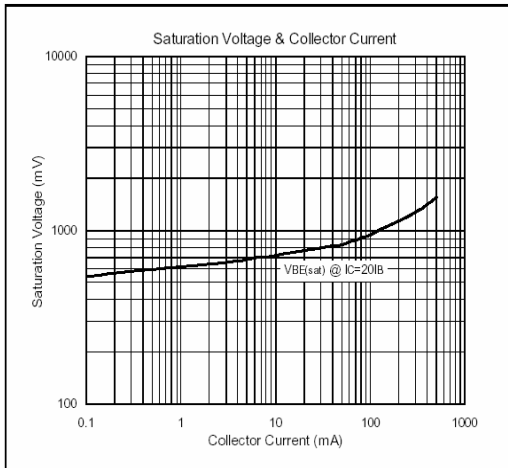
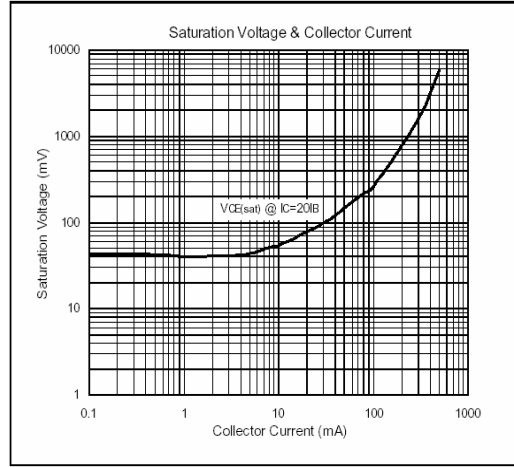
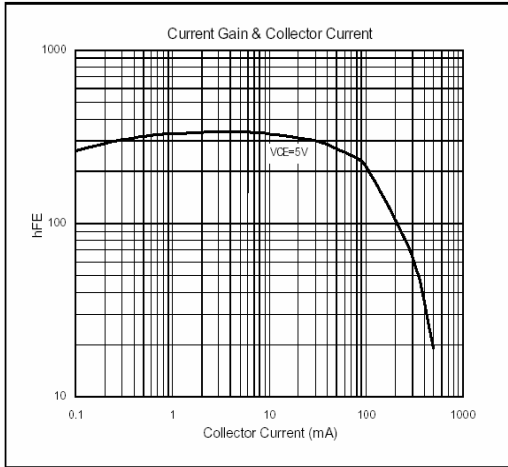
Characteristics at Ta = 25°C

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------|------|------|------|------|---|
| BVCBO | -30 | - | - | V | I _C =-100uA |
| BVCEO | -30 | - | - | V | I _C =-1mA |
| BVEBO | -5 | - | - | V | I _E =-10uA |
| ICBO | - | - | -15 | nA | V _{CB} =-30V |
| VCE(sat)1 | - | -90 | -300 | mV | I _C =-10mA, I _B =-0.5mA |
| VCE(sat)2 | - | -250 | -650 | mV | I _C =-100mA, I _B =-5mA |
| VBE(sat)1 | - | -700 | - | mV | I _C =-10mA, I _B =-0.5mA |
| VBE(sat)2 | - | -900 | - | mV | I _C =-100mA, I _B =-5mA |
| VBE(on)1 | -600 | - | -750 | mV | V _{CE} =-5V, I _C =-2mA |
| VBE(on)2 | - | - | -820 | mV | V _{CE} =-5V, I _C =-10mA |
| hFE | 110 | - | 800 | | V _{CE} =-5V, I _C =-2mA |
| f _T | - | 150 | - | MHz | V _{CE} =-5V, I _C =-10mA, f=100MHz |
| C _{ob} | - | - | 6 | pF | V _{CB} =-10V, f=1MHz, I _E =0A |

Classification Of hFE

| Rank | 9CA | 9CB | 9CC |
|-------|-----------|-----------|-----------|
| Range | 110 - 220 | 200 - 450 | 420 - 800 |

Characteristics Curve



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